Standard Rectifier Module

MDMA50P1200TG

preliminary

= 2x 1200 V

50 A

1.11V

Phase leg

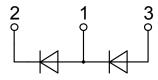
Part number

MDMA50P1200TG



Backside: isolated





Features / Advantages:

- Package with DCB ceramic base plate
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
 Field supply for DC motors
- Package: TO-240AA
- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- · Advanced power cycling



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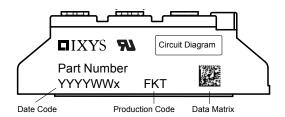
Rectifie	r				Ratings	3	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			1300	V
V _{RRM}	max. repetitive reverse blocking v	roltage	$T_{VJ} = 25^{\circ}C$			1200	V
I _R	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			100	μΑ
		V _R = 1200 V	$T_{VJ} = 150^{\circ}C$			1.5	mΑ
V _F	forward voltage drop	I _F = 50 A	$T_{VJ} = 25^{\circ}C$			1.18	V
		I _F = 100 A				1.39	٧
		I _F = 50 A	T _{VJ} = 125 °C			1.11	V
		$I_F = 100 \text{ A}$				1.38	V
I _{FAV}	average forward current	T _C = 100°C	T _{VJ} = 150°C			50	Α
		sine 180°					1
V _{F0}	threshold voltage		T _{VJ} = 150°C			0.82	٧
r _F	slope resistance \(\) for power in	oss calculation only				5.5	mΩ
R _{thJC}	thermal resistance junction to cas	e				0.65	K/W
R _{thCH}	thermal resistance case to heatsi	nk			0.20		K/W
P _{tot}	total power dissipation		$T_{c} = 25^{\circ}C$			190	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			850	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			920	Α
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C			725	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			780	Α
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			3.62	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			3.52	kA²s
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C			2.63	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			2.53	kA²s
CJ	junction capacitance	V _R = 400 V f= 1 MHz	$T_{VJ} = 25^{\circ}C$		27		pF



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Package	Package TO-240AA			Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	Α
T _{stg}	storage temperature				-40		125	°C
T _{VJ}	virtual junction temperature				-40		150	°C
Weight						90		g
M _D	mounting torque				2.5		4	Nm
M_{τ}	terminal torque				2.5		4	Nm
d _{Spp/App}	creepage distance on surface striking distance through a		terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on surface	Striking distance through an	terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second			4800			٧
		t = 1 minute	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		4000			٧



Part number

M = Module

D = Diode

M = Standard Rectifier

A = (up to 1800V)

50 = Current Rating [A]

P = Phase leg

1200 = Reverse Voltage [V] TG = TO-240AA

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA50P1200TG	MDMA50P1200TG	Box	6	513029

Equivalent Circuits for Simulation			* on die level	T _{VJ} = 150°C
$I \rightarrow V_0$	R_0	Rectifier		
V _{0 max}	threshold voltage	0.82		V
R _{0 max}	slope resistance *	4.3		$m\Omega$

preliminary

Outlines TO-240AA

